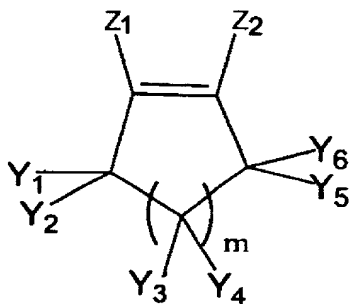


## ABSTRACT OF THE DISCLOSURE

Photoresist monomers of following Formula 1,  
photoresist polymers thereof, and photoresist  
compositions containing the same. The photoresist  
5 polymers include a repeating unit comprising the  
photoresist monomer of Formula 1 as a comonomer and the  
photoresist compositions containing the same have  
excellent etching resistance, heat resistance and  
adhesiveness to a wafer, and are developable in aqueous  
10 tetramethylammonium hydroxide (TMAH) solutions. In  
addition, the photoresist compositions have a low light  
absorbance at 157nm wavelength, and thus are suitable for  
a photolithography process using ultraviolet light  
sources such as VUV (157nm) in fabricating a minute  
15 circuit for a high integration semiconductor device.

Formula 1



wherein Y<sub>1</sub>, Y<sub>2</sub>, Y<sub>3</sub>, Y<sub>4</sub>, Y<sub>5</sub>, Y<sub>6</sub>, Z<sub>1</sub>, Z<sub>2</sub> and m are  
defined in the specification.